March 2010



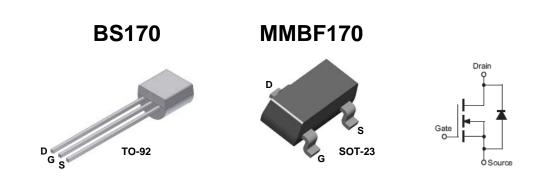
BS170 / MMBF170 N-Channel Enhancement Mode Field Effect Transistor

General Description

These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

Features

- High density cell design for low R_{DS(ON)}.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units	
V _{DSS}	Drain-Source Voltage	60		V	
V _{DGR}	Drain-Gate Voltage ($R_{GS} \le 1M\Omega$)	60		V	
V _{GSS}	Gate-Source Voltage	±	20	V	
I _D	Drain Current - Continuous	500	500	mA	
	- Pulsed	1200	800		
T _J , T _{STG}	Operating and Storage Temperature Range	- 55 1	to 150	°C	
ΤL	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	300		°C	

Thermal Characteristics $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
P _D	Maximum Power Dissipation Derate above 25°C	830 6.6	300 2.4	mW mW/°C
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	150	417	°C/W

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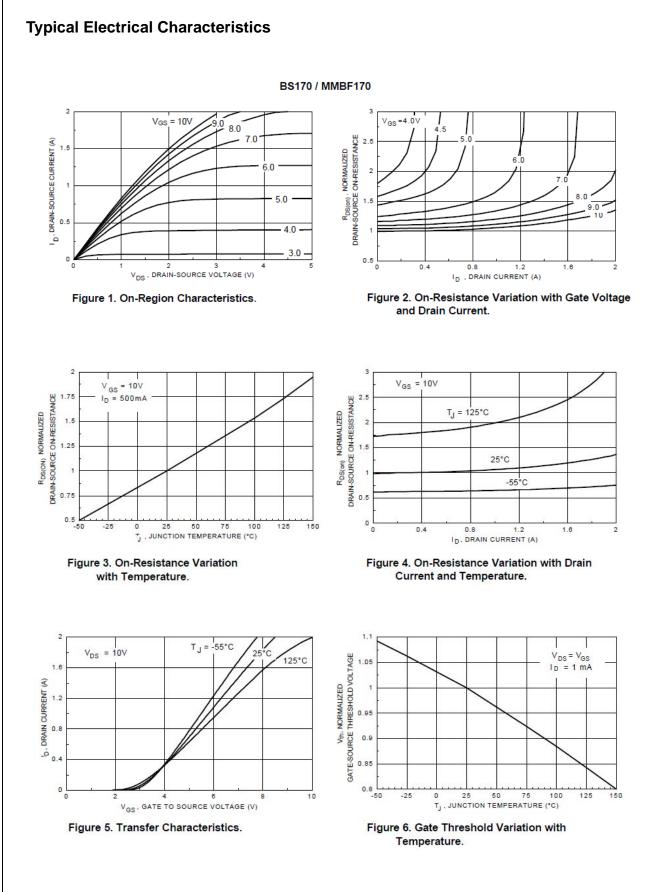
Symbol	Parameter	Conditions	Туре	Min.	Тур.	Max.	Units
OFF CHA	RACTERISTICS				1		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 100 \mu A$	All	60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 25V, V_{GS} = 0V$	All			0.5	μA
I _{GSSF}	Gate - Body Leakage, Forward	V _{GS} = 15V, V _{DS} = 0V	All			10	nA
ON CHAF	RACTERISTICS (Notes 1)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1mA$	All	0.8	2.1	3	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 200mA	All		1.2	5	Ω
g _{FS} Forward Tra	Forward Transconductance	V _{DS} = 10V, I _D = 200mA	BS170		320		mS
			MMBF170		320		
Dynamic	Characteristics	L					
C _{iss}	Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	All		24	40	pF
C _{oss}	Output Capacitance	f = 1.0MHz	All		17	30	pF
C _{rss}	Reverse Transfer Capacitance		All		7	10	pF
Switching	g Characteristics (Notes 1)						
t _{on}	Turn-On Time	$V_{DD} = 25V, I_D = 200mA, \\ V_{GS} = 10V, R_{GEN} = 25\Omega$	BS170			10	ns
		$V_{DD} = 25V, I_D = 500mA, \\ V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	
t _{off}	Turn-Off Time	V_{DD} = 25V, I_D = 200mA, V_{GS} = 10V, R_{GEN} = 25 Ω	BS170			10	ns
		$V_{DD} = 25V, I_D = 500mA, V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	

Note:

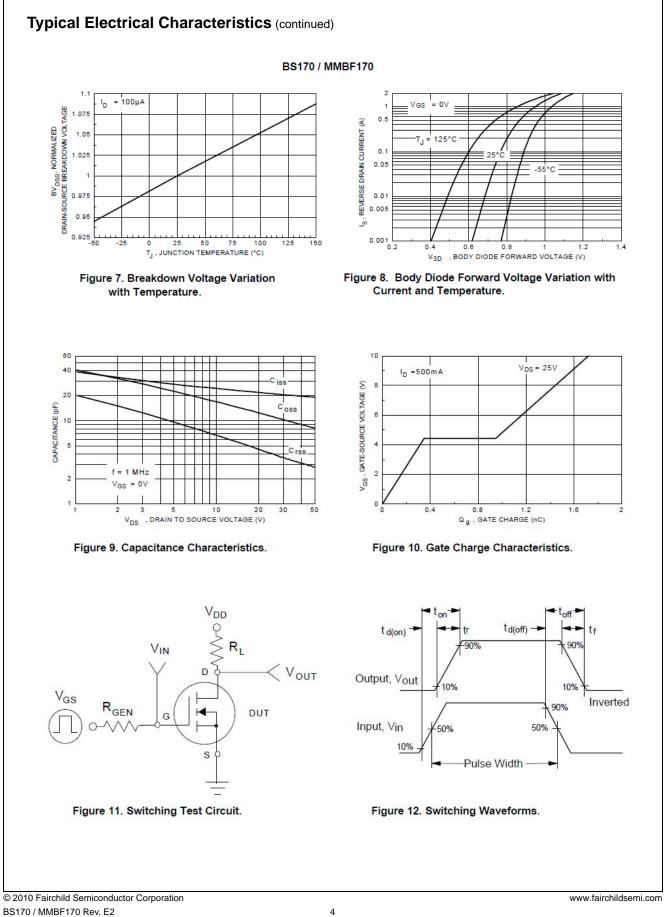
1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.

Ordering Information

Part Number	Package	Package Type	Lead Frame	Pin array
BS170	TO-92	BULK	STRAIGHT	DGS
BS170_D26Z	TO-92	Tape and Reel	FORMING	DGS
BS170_D27Z	TO-92	Tape and Reel	FORMING	DGS
BS170_D74Z	TO-92	AMMO	FORMING	DGS
BS170_D75Z	TO-92	AMMO	FORMING	DGS
MMBF170	SOT-23	Tape and Reel		

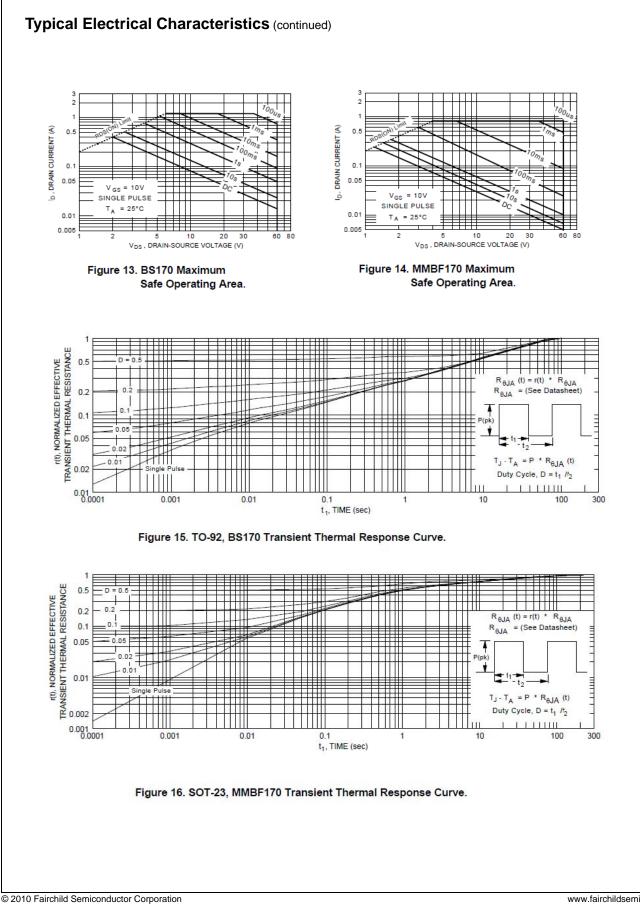


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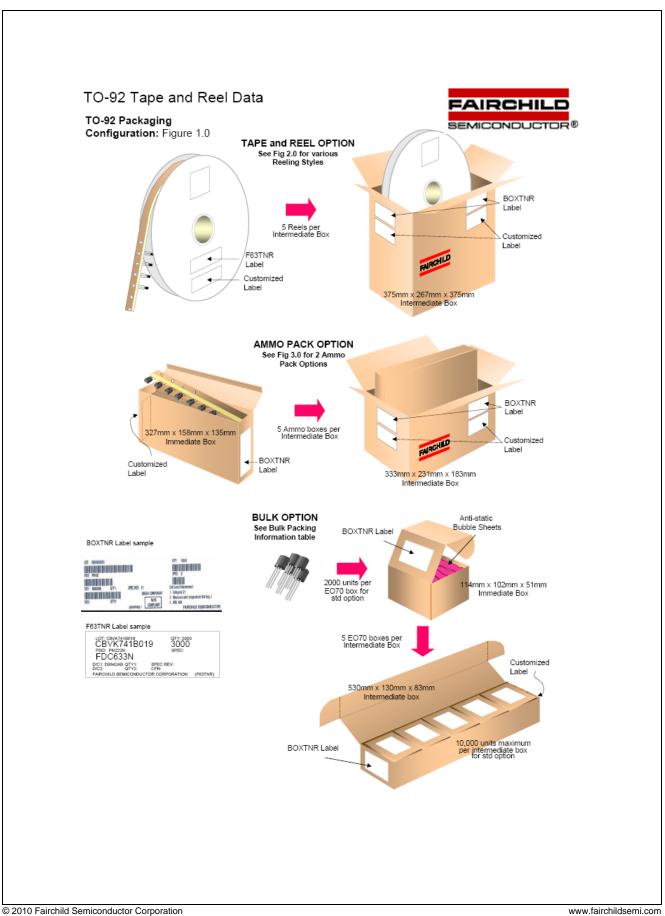
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TO-92 Tape and Reel Data, continued



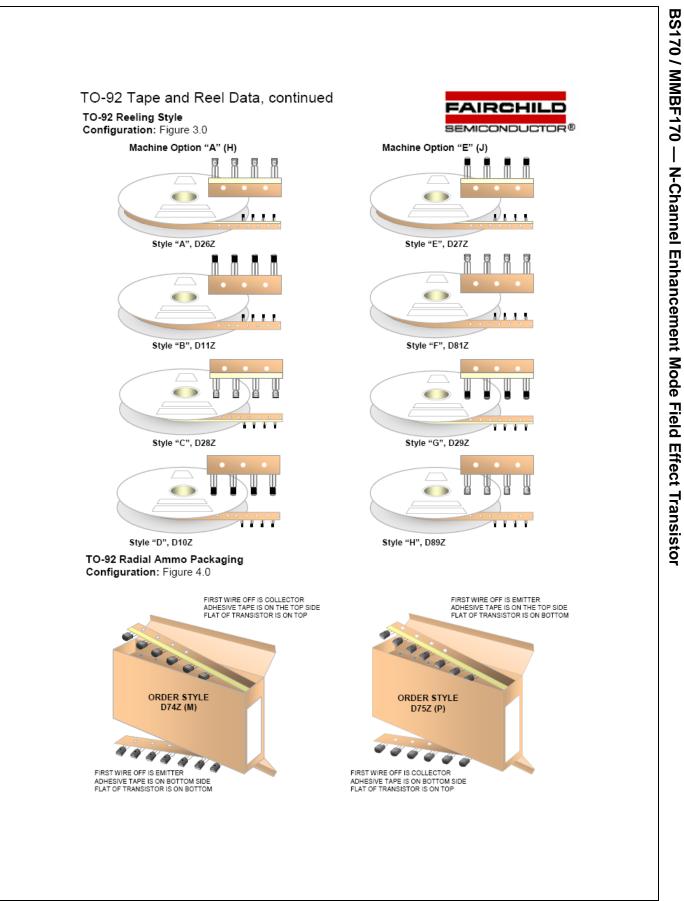
TO-92 Packing Information: Figure 2.0

TO-92 TNR/AM	IMO PACKIN	G INFORMATI	ON TABLE

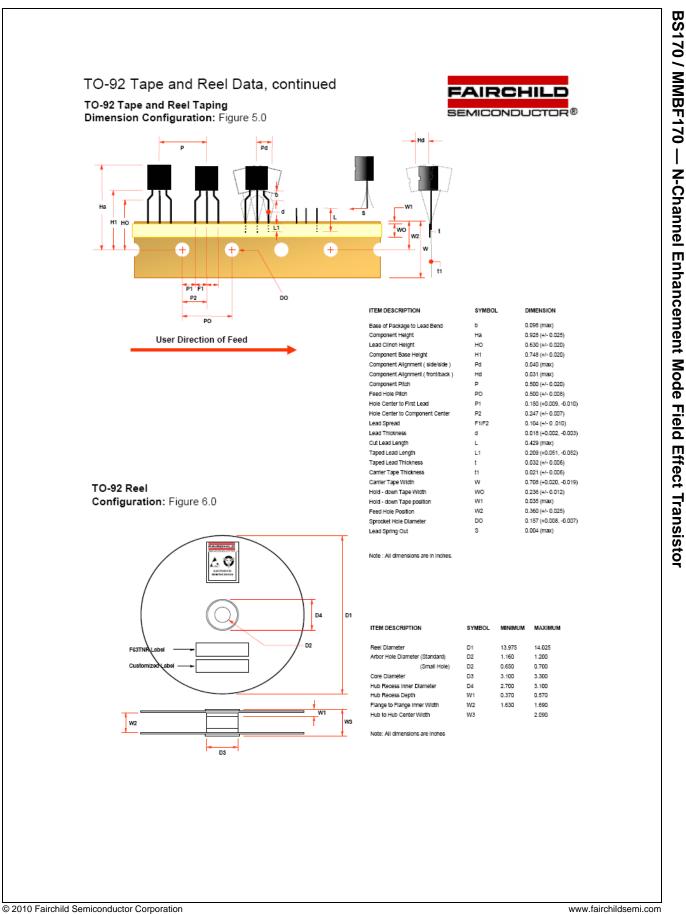
Packing	Style	Quantity	EOL code
Reel	Α	2,000	D26Z
	В	2,000	D11Z
	С	2,000	D28Z
	D	2,000	D10Z
	E	2,000	D27Z
	F	2,000	D81Z
	G	2,000	D29Z
	н	2,000	D89Z
Ammo	M	2,000	D74Z
	Р	2,000	D75Z
	ith components	= 0.22 gm = 1.04 kg = 1.02 kg ox = 10,000 units	

TO-92 BULK PACKING INFORMATION TABLE

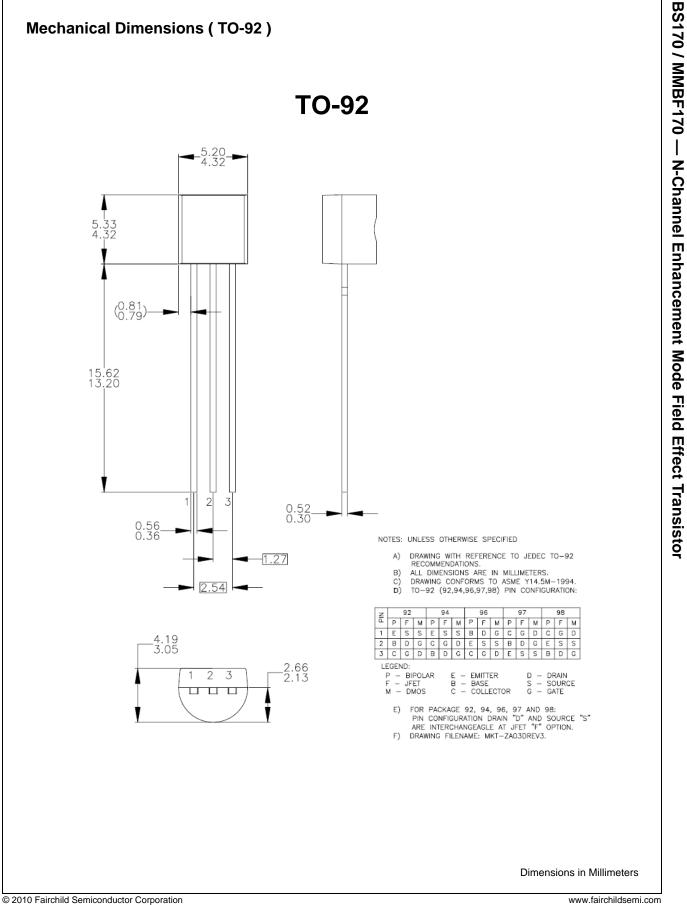
EOL CODE / FLOW OPTION	DESCRIPTION	LEADCLIP DIMENSION	MINIMUM ORDER QTY	LEADFORM OULTINE
NO EOL CODE	STRAIGHT LEADS	NO LEAD CLIP	2.0K / BOX	×.
J18Z	TO-18 OPTION STD	NO LEAD CLIP	2.0K / BOX	
J35Z	TO-18 OPTION REVERSE	NO LEAD CLIP	2.0K / BOX	
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5K / BOX	
J60Z	TO-5 OPTION REVERSE	NO LEAD CLIP	1.5K / BOX	
J61Z	IN LINE 0.200 SPACING	NO LEAD CLIP	1.5K / BOX	



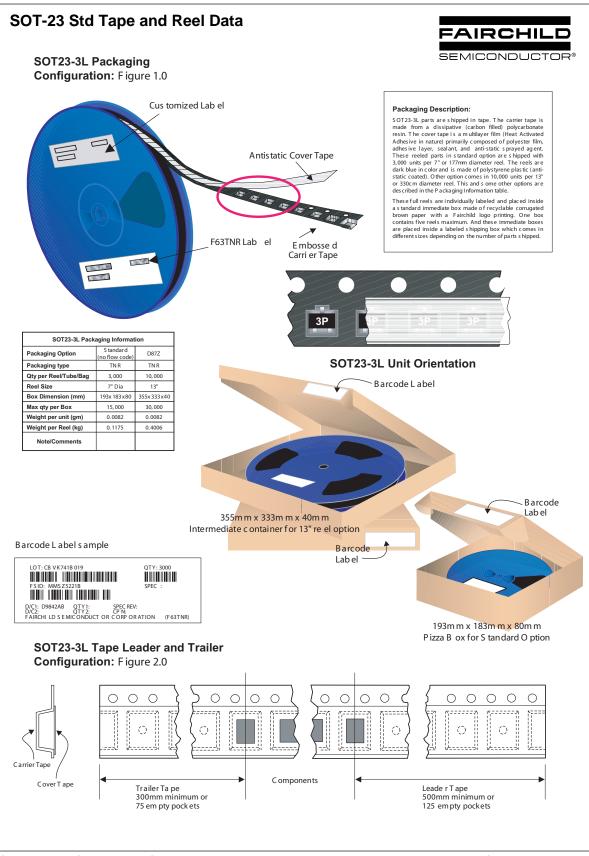
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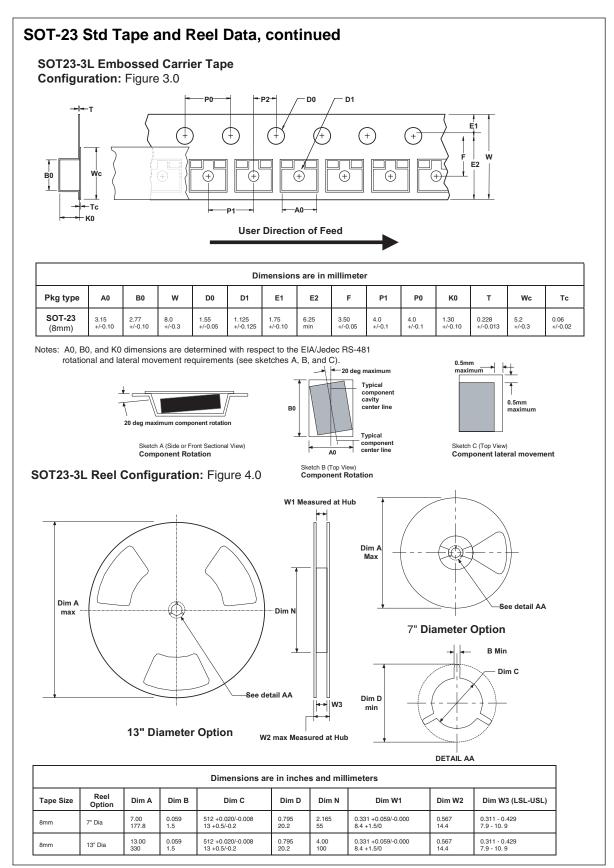


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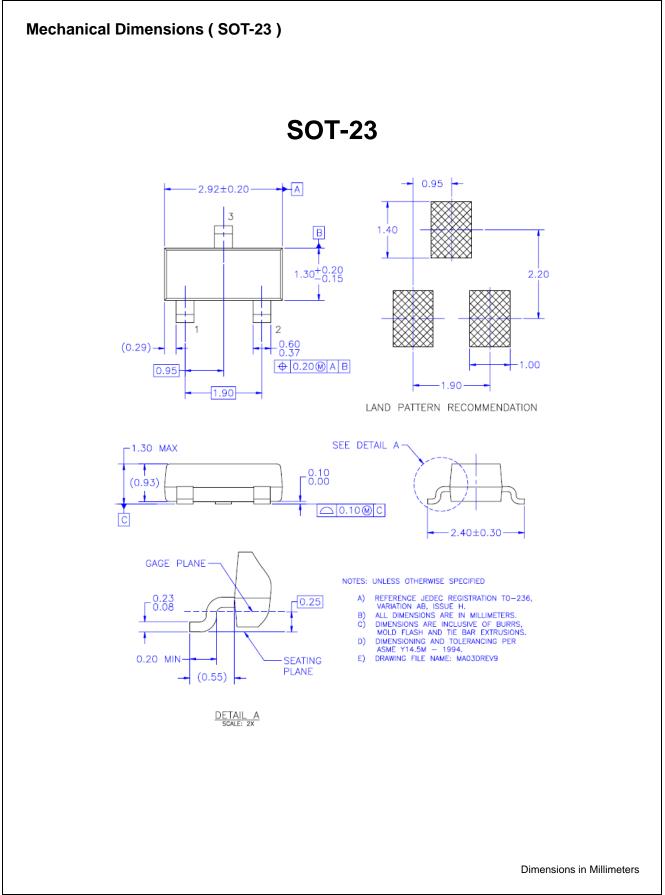


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October 2004, Rev. D1



October 2004, Rev. D1



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PRODUCT STATUS DEFINITIONS

Definition	of Tormo	

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.
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